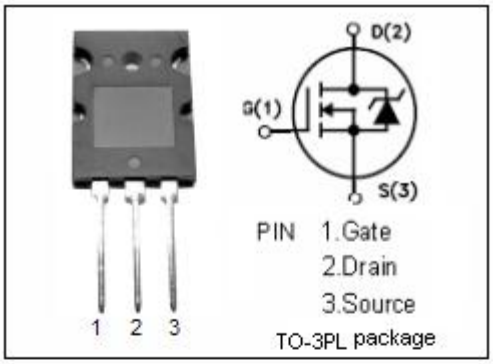
isc N-Channel MOSFET Transistor 2SK1466



DESCRIPTION

- Drain Current –I_D=16A@ T_C=25℃
- Drain Source Voltage-
  : V_{DSS}=900 (Min)
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

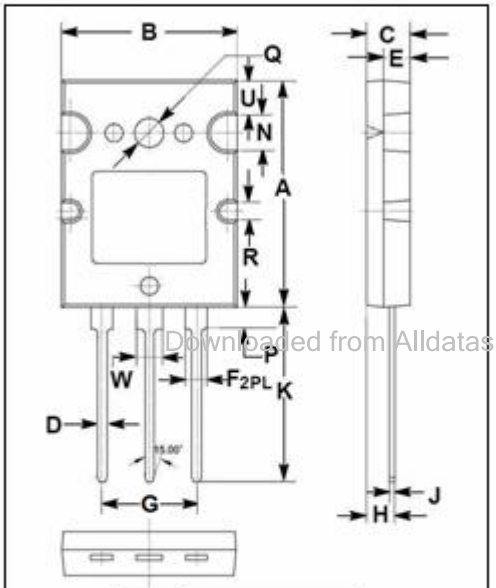
- Designed for high voltage, high speed power switching

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage (V_{GS}=0)	900	V
V_{GS}	Gate-Source Voltage	±30	V
I_D	Drain Current-continuous@ TC=25℃	16	A
P_{tot}	Total Dissipation@TC=25℃	250	W
T_j	Max. Operating Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth j-c	Thermal Resistance,Junction to Case	1.25	℃/W
Rth j-a	Thermal Resistance,Junction to Ambient	35.0	℃/W



DIM	mm MIN	mm MAX
A	25.50	26.50
B	19.80	20.20
C	4.50	5.50
D	0.90	1.10
E	2.80	3.20
F	2.40	2.60
G	10.80	11.00
H	3.10	3.30
J	0.50	0.70
K	20.00	21.00
N	3.90	4.50
P	2.40	2.60
Q	3.10	3.50
R	1.90	2.60
U	3.90	4.10
W	2.90	3.25

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• **ELECTRICAL CHARACTERISTICS (T_C=25℃)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0; I_D= 10mA	900			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=10V; I_D=1mA	2.0		3.0	V
$R_{DS(on)}$	Drain-Source On-stage Resistance	V_{GS}=10V; I_D=8A		0.6	0.8	Ω
I_{GSS}	Gate Source Leakage Current	V_{GS}= ±30V;V_{DS}= 0			±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=900V; V_{GS}= 0			1	mA
V_{SD}	Diode Forward Voltage	I_F=16A; V_{GS}=0			1.8	V
tr	Rise time	V_{GS}=10V;I_D=8A;R_L=50Ω		120		ns
ton	Turn-on time			155		ns
tf	Fall time			200		ns
toff	Turn-off time			1050		ns

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